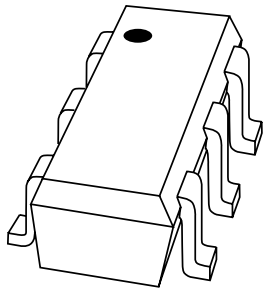


# DATA SHEET



## **BC847BPN** NPN/PNP general purpose transistor

Product specification  
Supersedes data of 1999 Apr 26

2001 Oct 26

# NPN/PNP general purpose transistor

# BC847BPN

### FEATURES

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and boardspace
- No mutual interference between the transistors.

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

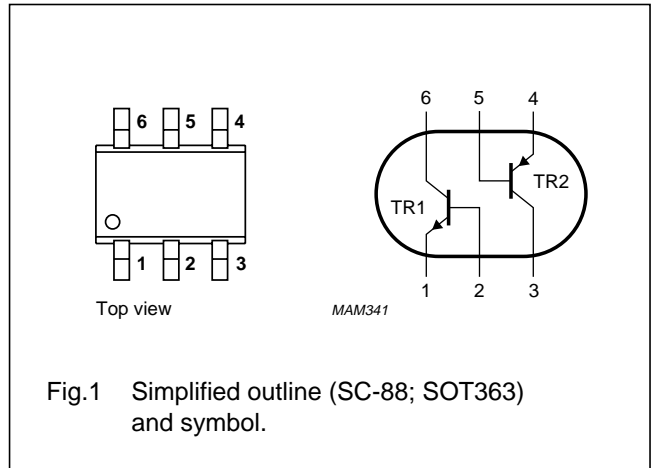
NPN/PNP transistor pair in an SC-88; SOT363 plastic package.

### MARKING

TYPE NUMBER	MARKING CODE
BC847BPN	13t

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
6, 3	collector TR1; TR2



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>					
$V_{CBO}$	collector-base voltage	open emitter	–	50	V
$V_{CEO}$	collector-emitter voltage	open base	–	45	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	200	mA
$I_{BM}$	peak base current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	200	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW

### Note

1. Device mounted on an FR4 printed-circuit board.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
<b>Per device</b>				
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

## Note

1. Device mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

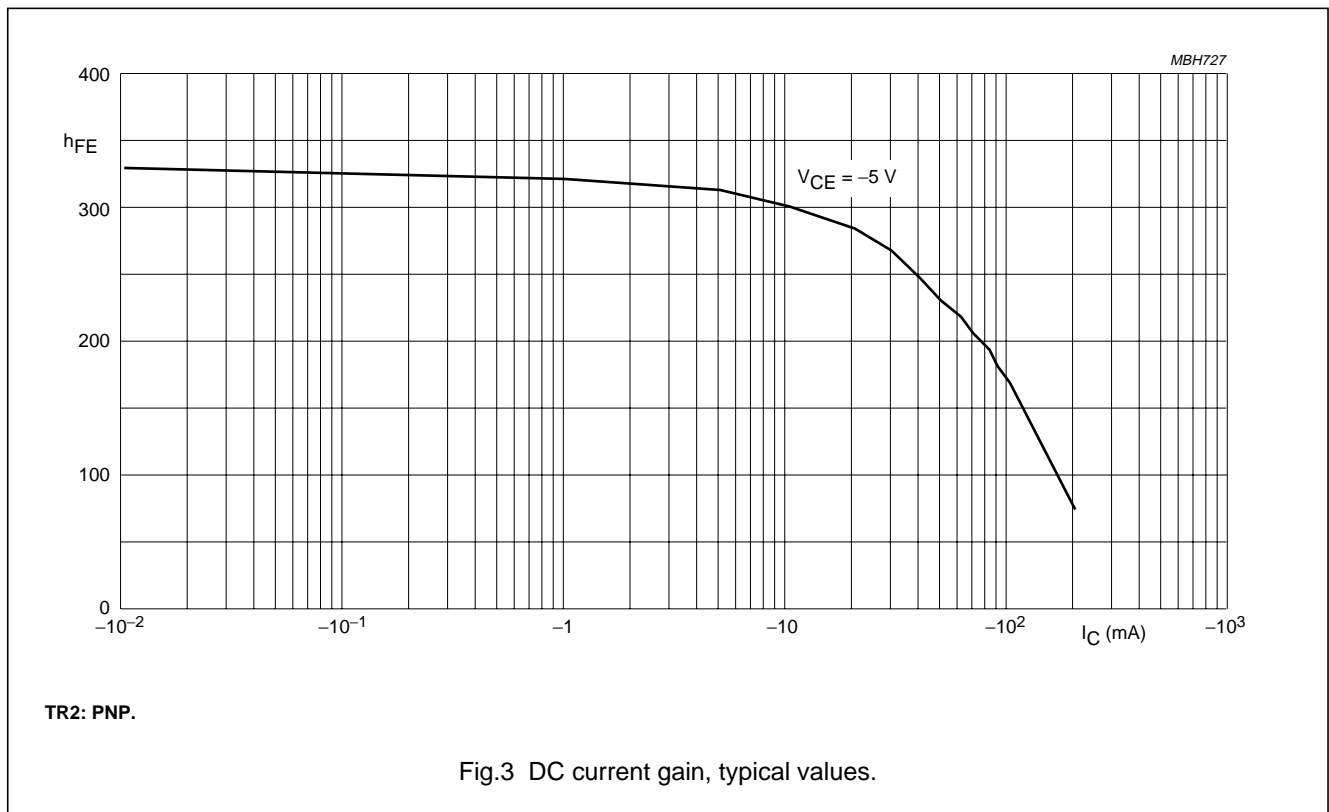
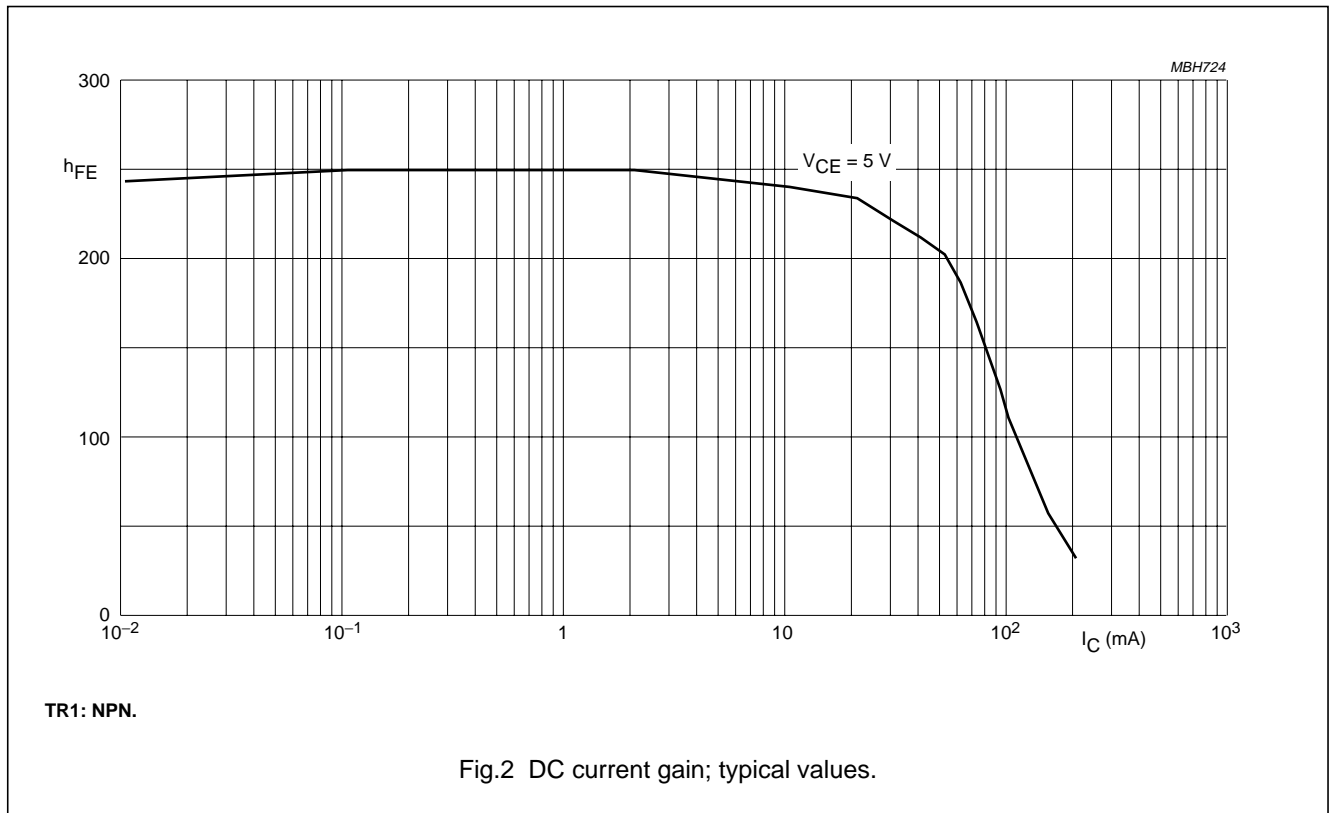
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per transistor unless otherwise specified; for the PNP transistor with negative polarity</b>						
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	5	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	200	–	450	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	100	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	–	300	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	755	–	mV
$V_{BE}$	base-emitter voltage TR1 NPN TR2 PNP	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	580	655	700	mV
			600	655	750	mV
$C_c$	collector capacitance TR1 NPN TR2 PNP	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	1.5	pF
			–	–	2.2	pF
$C_e$	emitter capacitance TR1 NPN TR2 PNP	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	11	–	pF
			–	10	–	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

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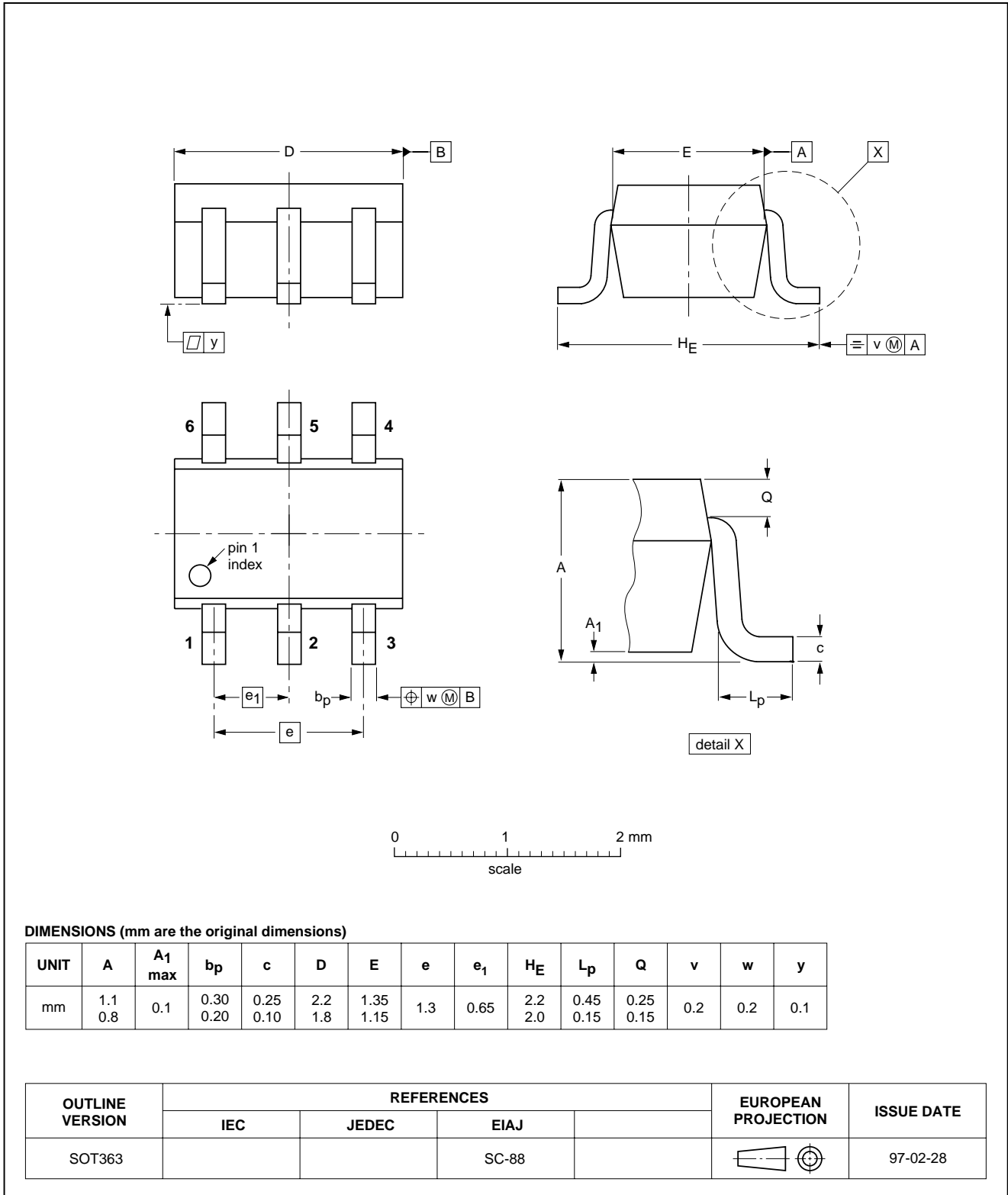
NPN/PNP general purpose transistor

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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



## NPN/PNP general purpose transistor

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## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

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BC847BPN

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**NOTES**

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